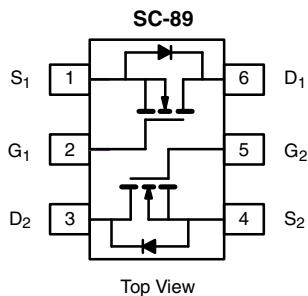


## N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (mA)
20	5 at $V_{GS} = 4.5$ V	200
	7 at $V_{GS} = 2.5$ V	175
	9 at $V_{GS} = 1.8$ V	150
	10 at $V_{GS} = 1.5$ V	50



Marking Code: L

**Ordering Information:** Si1034X-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET: 1.5 V Rated
- Low-Side Switching
- Low On-Resistance: 5  $\Omega$
- Low Threshold: 0.9 V (typ.)
- Fast Switching Speed: 35 ns (typ.)
- 1.5 V Operation
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

### BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

### APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	20		V	
Gate-Source Voltage	$V_{GS}$	$\pm 5$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	190	180	mA
		$T_A = 85$ °C	140	130	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	650			
Continuous Source Current (Diode Conduction)	$I_S$	450	380		
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	280	250	mW
		$T_A = 85$ °C	145	130	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000		V	

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

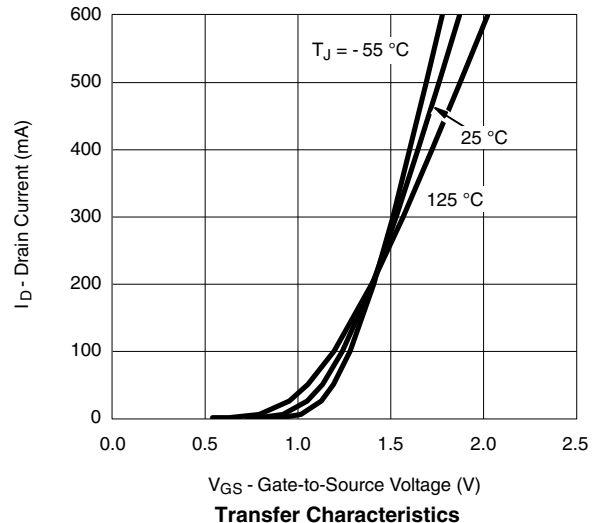
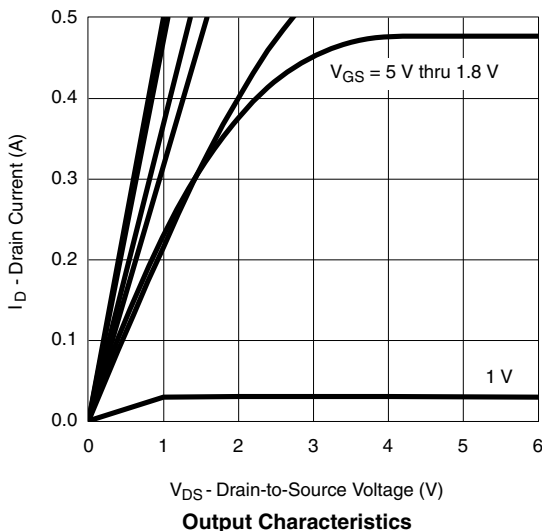
SPECIFICATIONS (T <sub>A</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.40		1.2	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 2.8 V		± 0.5	± 1.0	μA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 4.5 V		± 1.0	± 3.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V		1	500	nA
		V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			10	μA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 4.5 V	250			mA
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 200 mA			5	Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 175 mA			7	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 150 mA			9	
		V <sub>DS</sub> = 1.5 V, I <sub>D</sub> = 40 mA			10	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 200 mA		0.5		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 150 mA, V <sub>GS</sub> = 0 V			1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 150 mA		750		pC
Gate-Source Charge	Q <sub>gs</sub>			75		
Gate-Drain Charge	Q <sub>gd</sub>			225		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, R <sub>L</sub> = 47 Ω I <sub>D</sub> ≅ 200 mA, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 10 Ω			50	ns
Rise Time	t <sub>r</sub>				25	
Turn-Off Delay Time	t <sub>d(off)</sub>				50	
Fall Time	t <sub>f</sub>				25	

Notes:

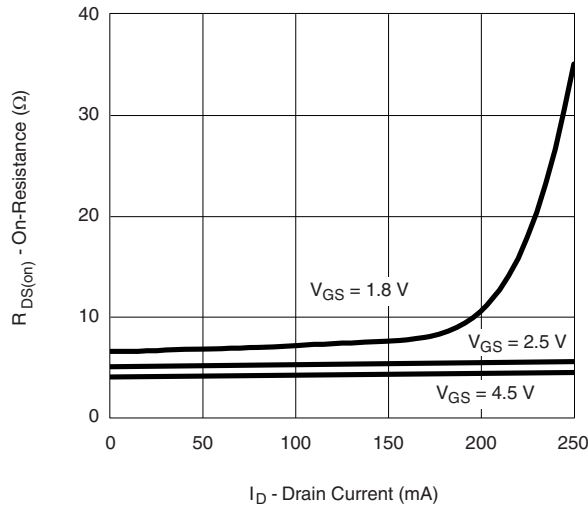
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

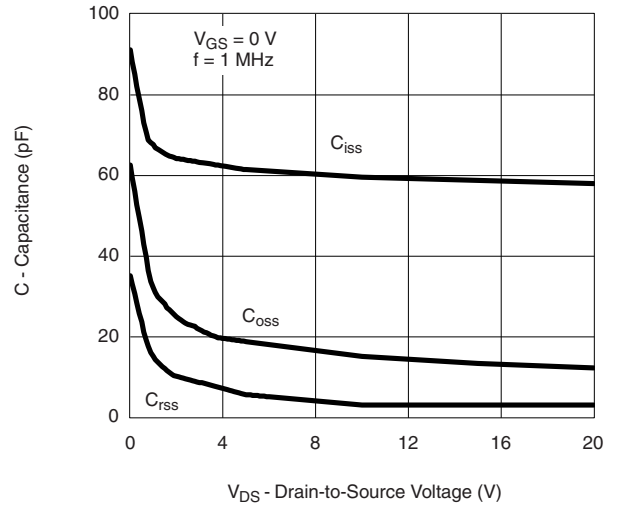
**TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



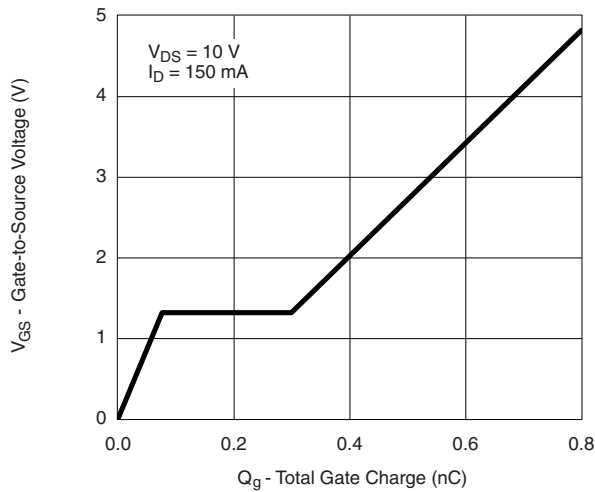
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



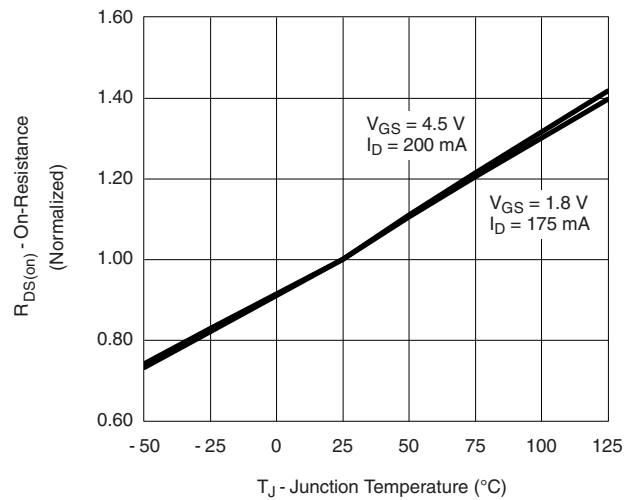
**On-Resistance vs. Drain Current**



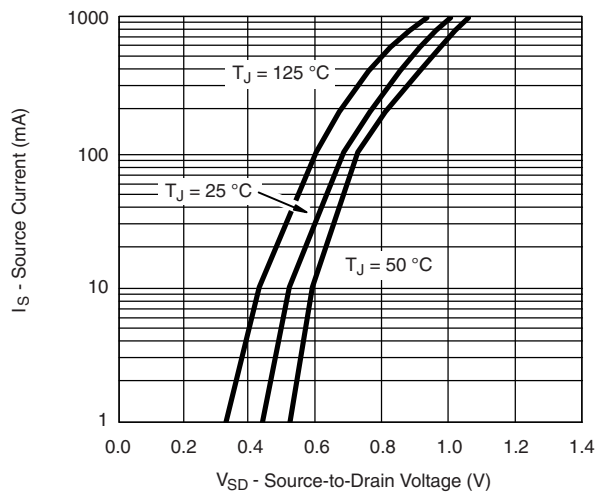
**Capacitance**



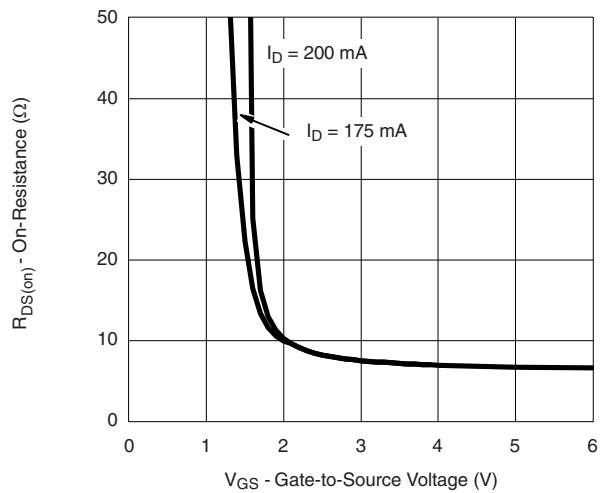
**Gate Charge**



**On-Resistance vs. Junction Temperature**

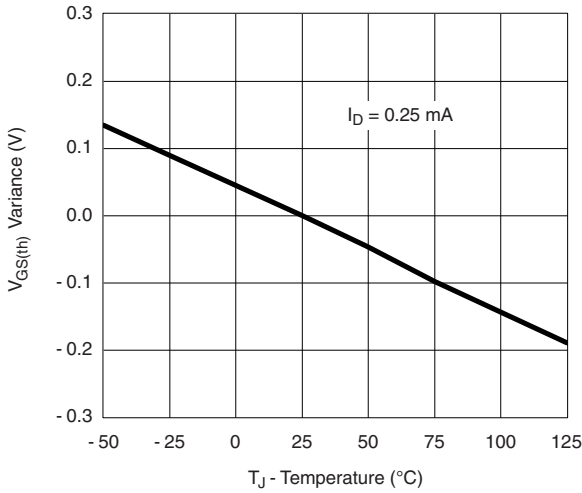


**Surge-Drain Diode Forward Voltage**

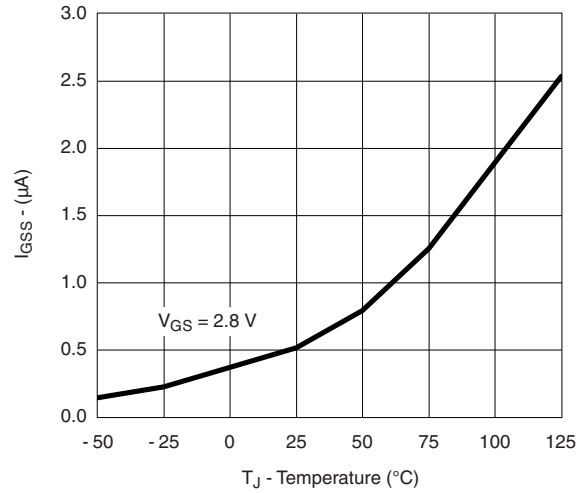


**On-Resistance vs. Gate-to-Source Voltage**

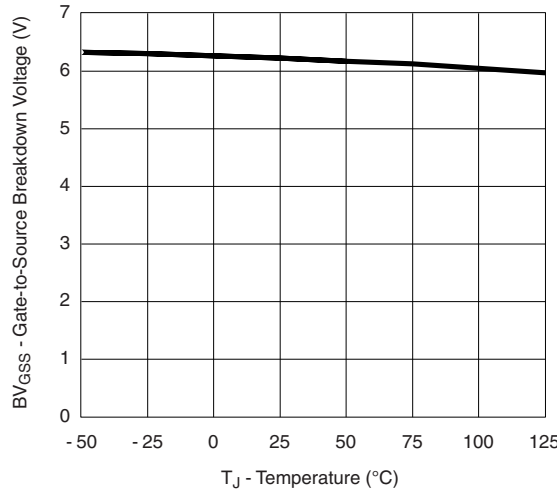
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



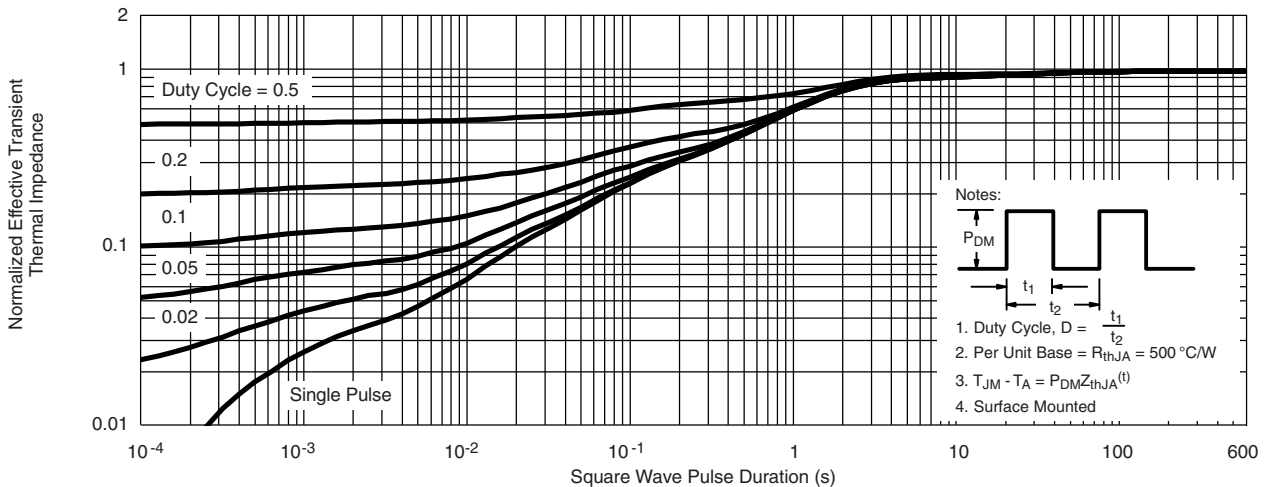
**Threshold Voltage Variance vs. Temperature**



**I<sub>GSS</sub> vs. Temperature**



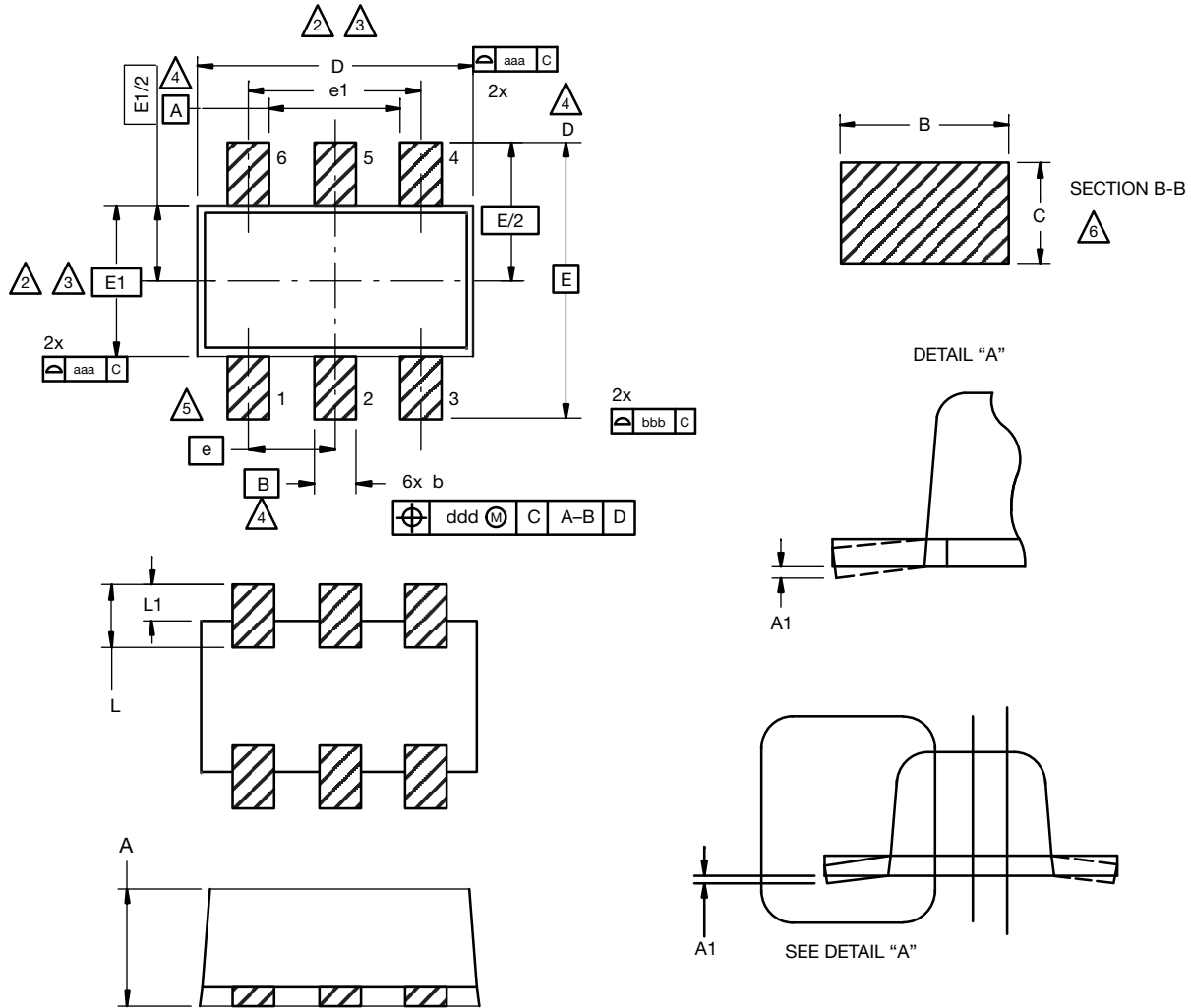
**BV<sub>GSS</sub> vs. Temperature**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

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## SC-89 6-Leads (SOT-563F)



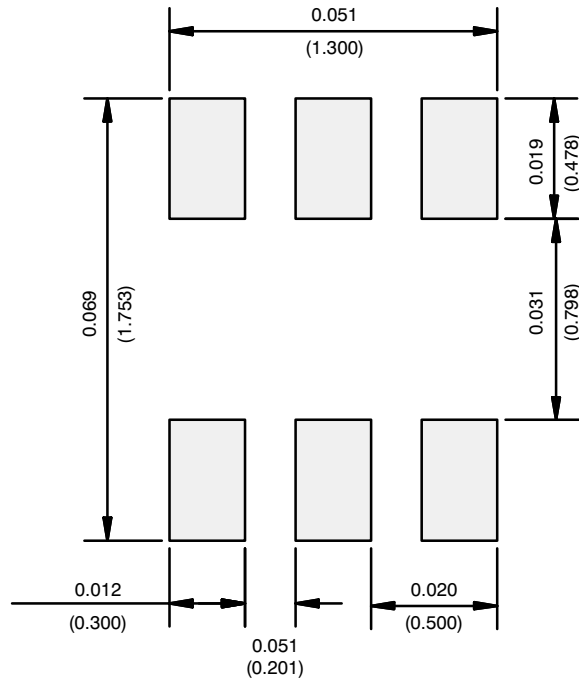
### Notes

1. Dimensions in millimeters.
- ⚠ Dimension D does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.
- ⚠ Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.
- ⚠ Datums A, B and D to be determined 0.10 mm from the lead tip.
- ⚠ Terminal numbers are shown for reference only.
- ⚠ These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.56	0.58	0.60
A1	0	0.02	0.10
b	0.15	0.22	0.30
c	0.10	0.14	0.18
D	1.50	1.60	1.70
E	1.50	1.60	1.70
E1	1.15	1.20	1.25
e	0.45	0.50	0.55
e1	0.95	1.00	1.05
L	0.25	0.35	0.50
L1	0.10	0.20	0.30

C14-0439-Rev. C, 11-Aug-14  
DWG: 5880

## RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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